

Silicon NPN Power Transistors

2SC1723

DESCRIPTION

- With TO-220C package
- High breakdown voltage
- High transition frequency

APPLICATIONS

- Low frequency high voltage power amplifier
- TV power supply driver

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

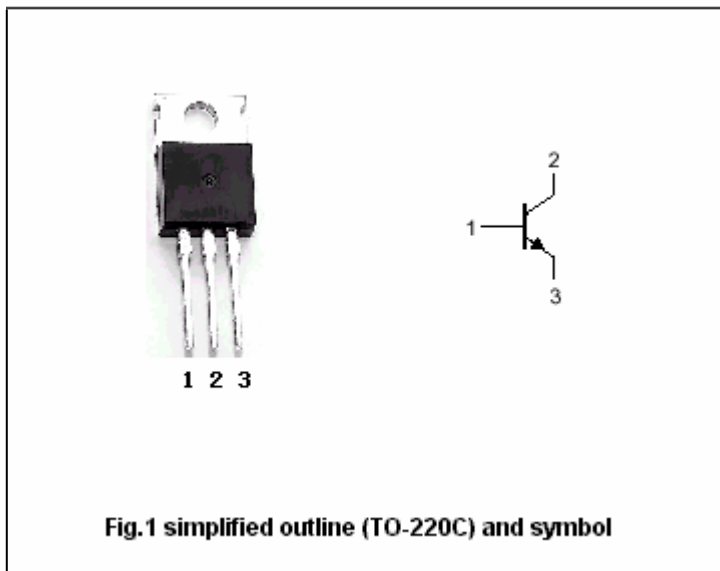


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	300	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		0.2	A
P _C	Collector power dissipation	T _C =25°C	15	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-45~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA ; R _{BE} =∞	300			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =100μA ; I _E =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =100μA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =100mA ; I _B =10mA		0.32	1.5	V
V _{BE}	Base-emitter on voltage	I _C =50m A ; V _{CE} =10V		0.66	0.9	V
I _{CBO}	Collector cut-off current	V _{CB} =250V ; I _E =0			0.1	μA
I _{CEO}	Collector cut-off current	V _{CE} =250V ; R _{BE} =∞			2	μA
h _{FE}	DC current gain	I _C =50m A ; V _{CE} =10V	40		200	
f _T	Transition frequency	I _C =30m A ; V _{CE} =20V		60		MHz
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =50V ; f=1MHz		6.2		pF

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PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)